

BOX AFTER FINAL  
EXPEDITED PROCEDURE  
740756-1638

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



The PATENT application of: ) Art Unit: 2813  
Hisashi OHTANI et al. ) Examiner: Evan PERT  
Application No.: 08/807,737 )  
Filed: February 27, 1997 )  
For: METHOD FOR MANUFACTURING )  
SEMICONDUCTOR DEVICE )

AMENDMENT AFTER FINAL UNDER 37 C.F.R. 1.116

Commissioner of Patents  
Washington, D.C. 20231

September 19, 2001

Dear Sir:

In response to the Examiner's Final Office Action mailed May 9, 2001, please consider the following remarks in connection with the above-identified application.

IN THE CLAIMS:

Please amend claim 84 as follows:

84. (Amended) A method of manufacturing a semiconductor device comprising the steps of:  
forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;  
depositing a semiconductor film comprising amorphous silicon on said silicon nitride film;  
disposing a metal contact with at least a selected portion of said semiconductor film;

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